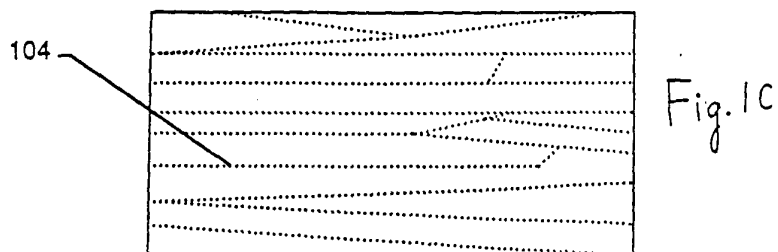
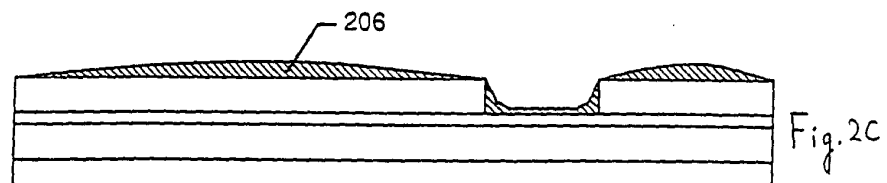
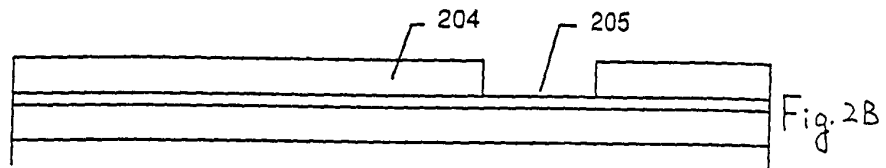
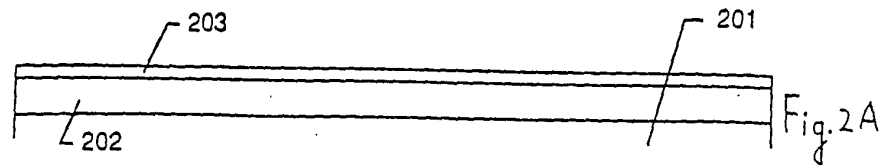


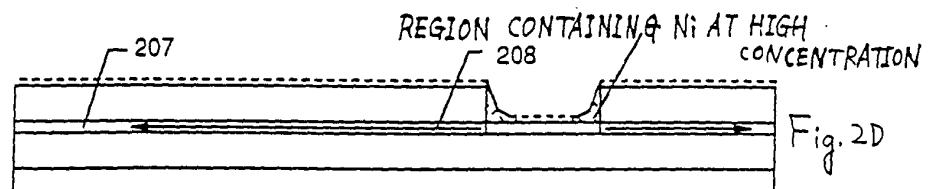
ILLUMINATION WITH
LASER LIGHT OR STRONG LIGHT



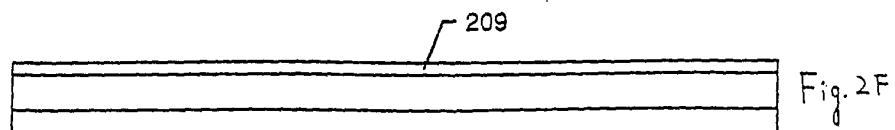
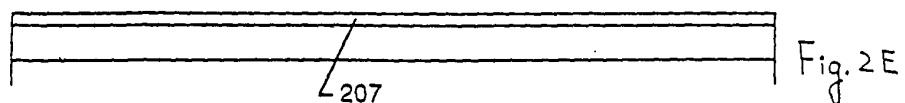
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SEMICONDUCTOR THIN FILM AND ITS MANUFACTURING
METHOD AND SEMICONDUCTOR DEVICE AND ITS
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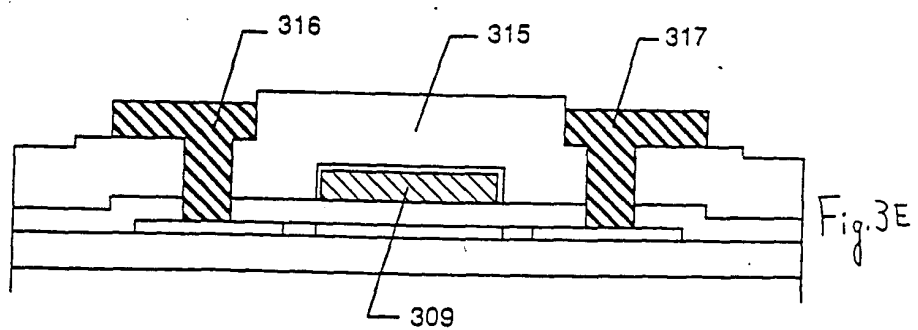
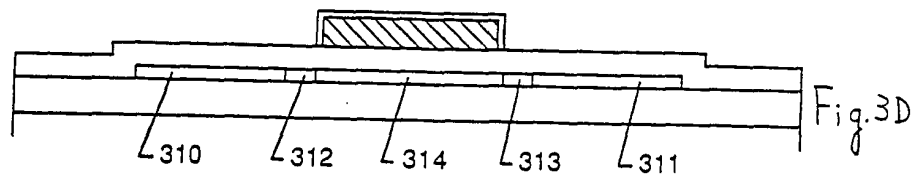
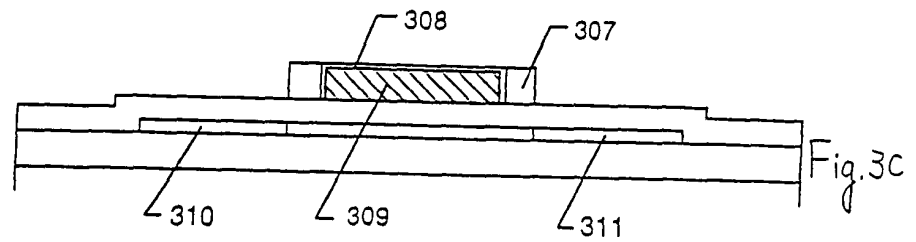
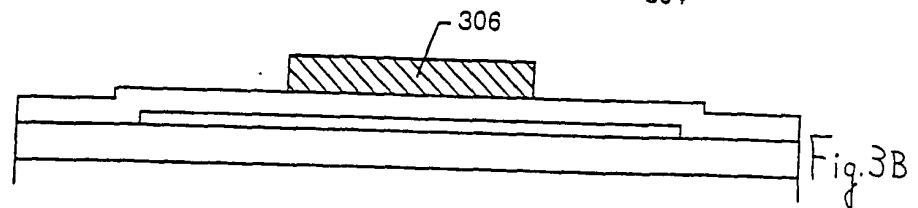
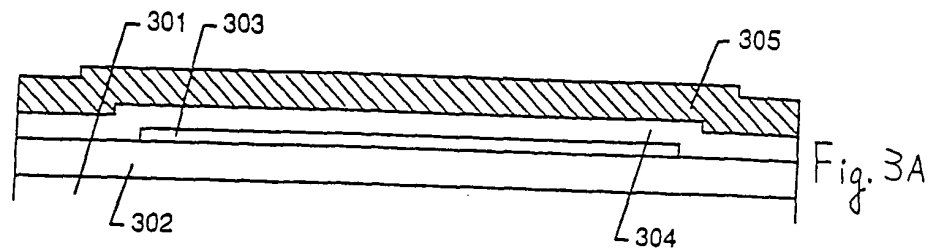
HEAT TREATMENT FOR CRYSTALLIZATION



ILLUMINATION WITH LASER LIGHT OR STRONG LIGHT



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SEMICONDUCTOR THIN FILM AND ITS MANUFACTURING
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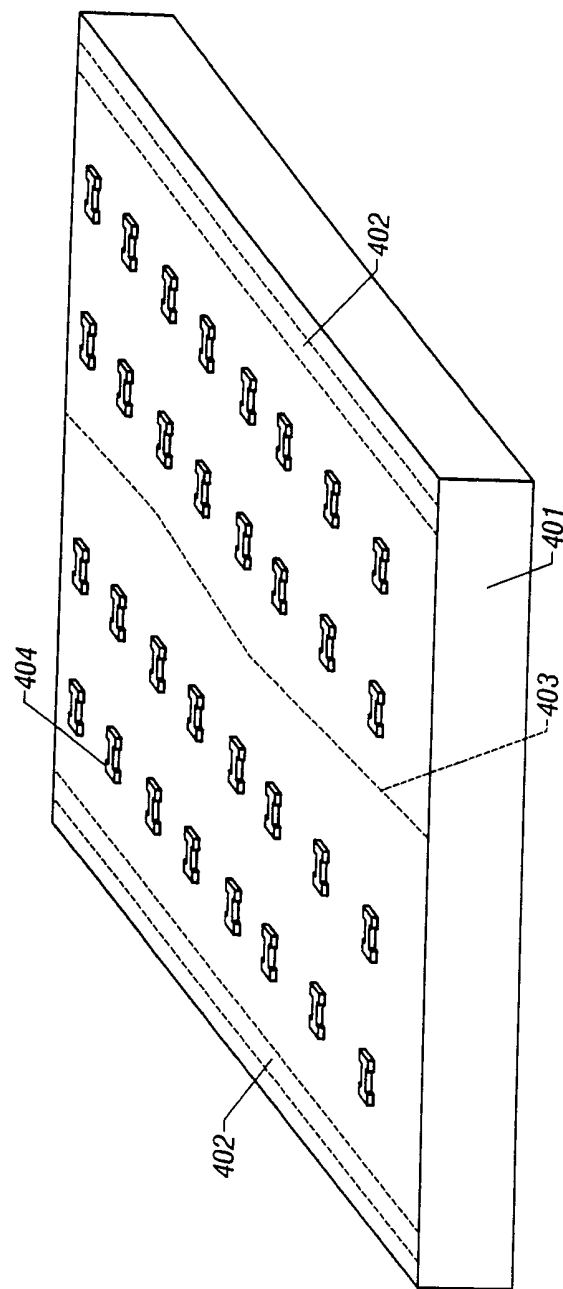
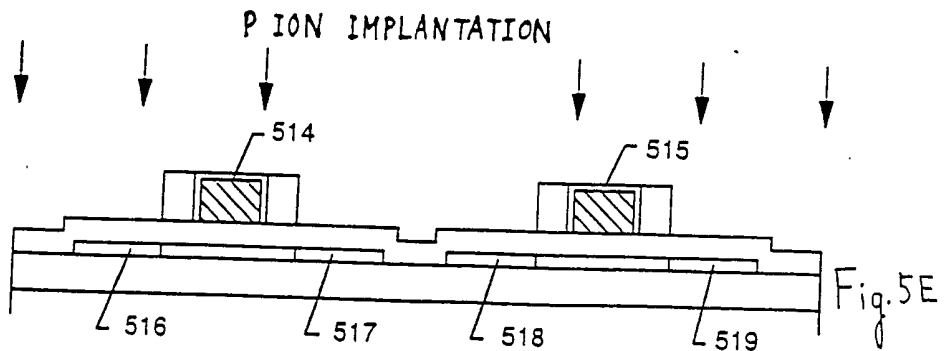
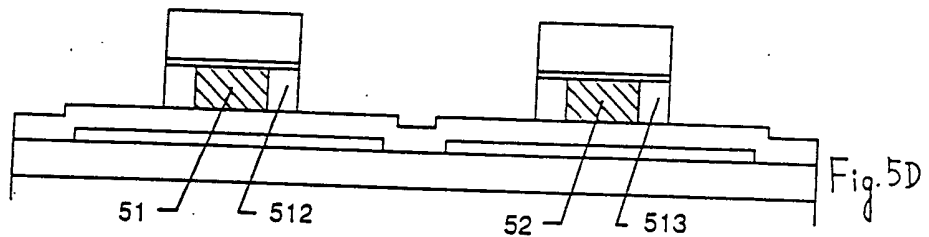
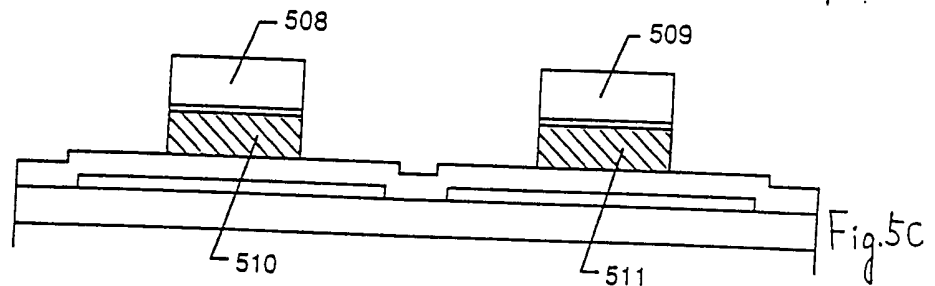
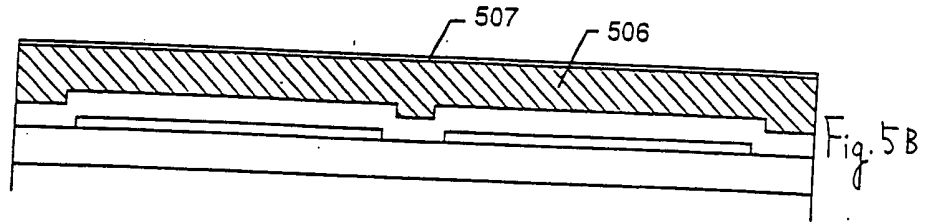
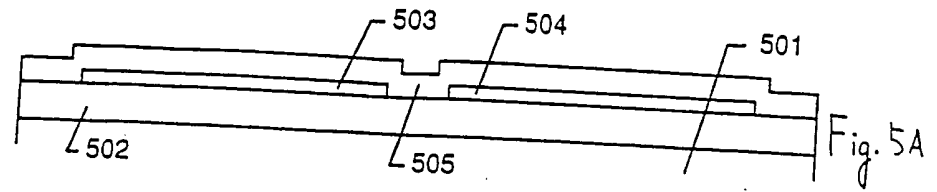
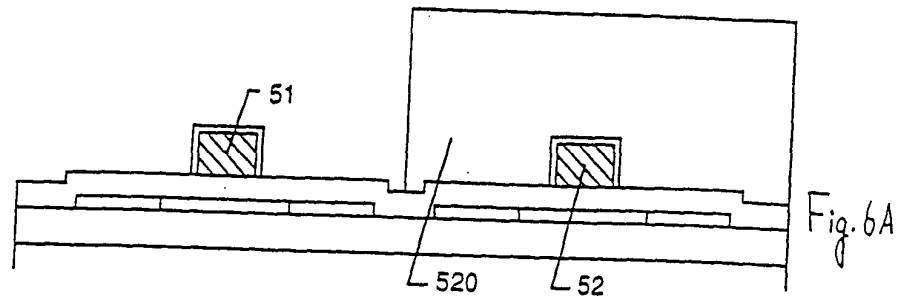
SEMICONDUCTOR THIN FILM AND ITS MANUFACTURING
METHOD AND SEMICONDUCTOR DEVICE AND ITS
MANUFACTURING METHOD

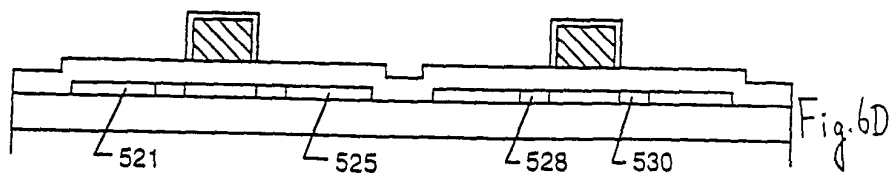
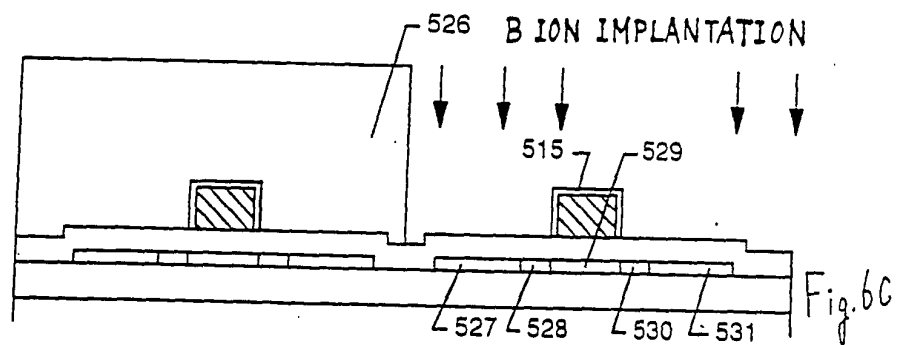
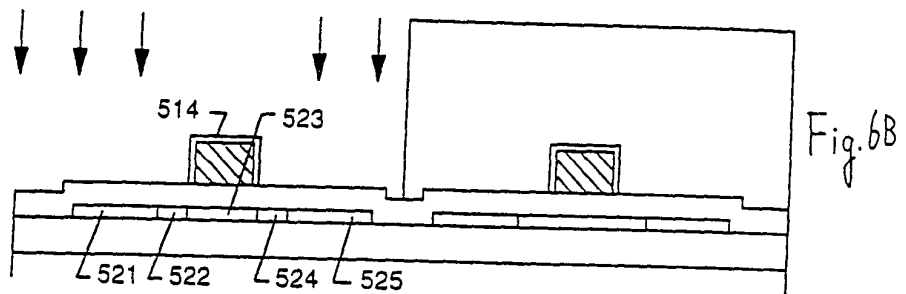
FIG. 4

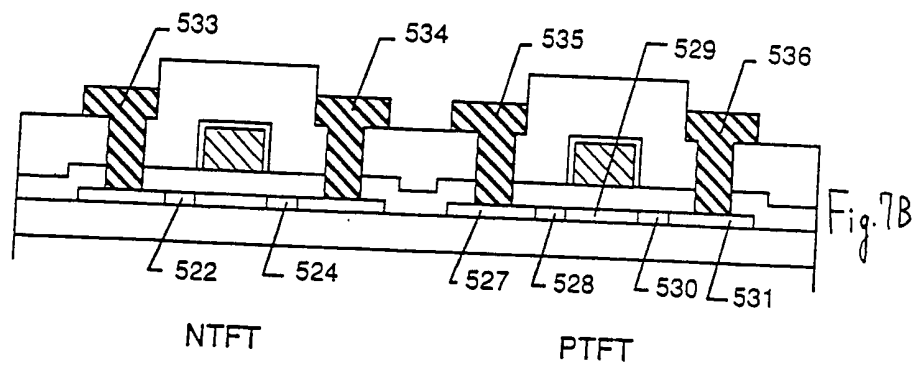
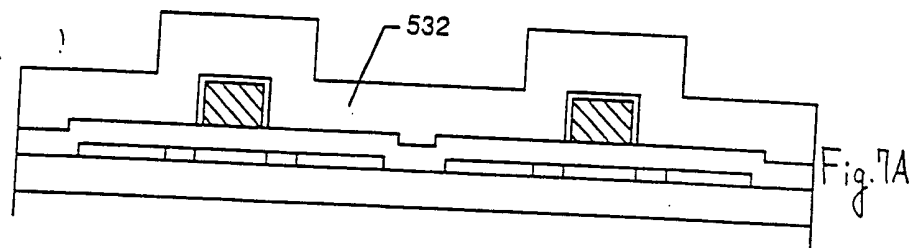


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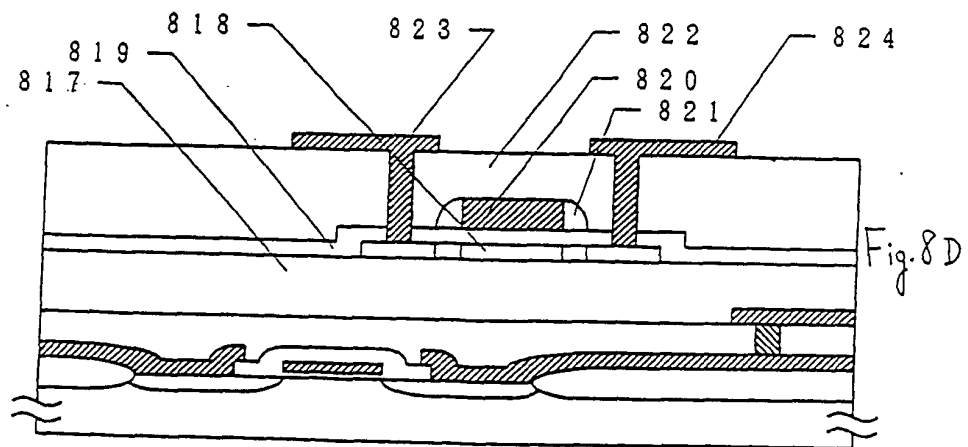
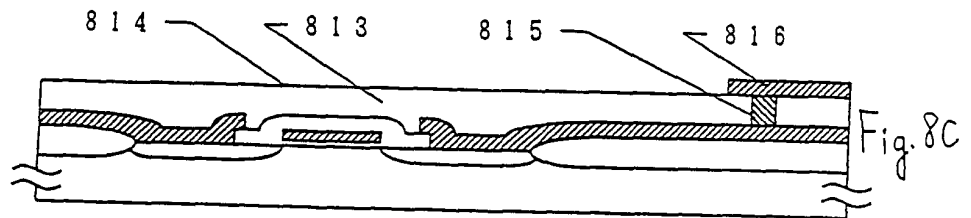
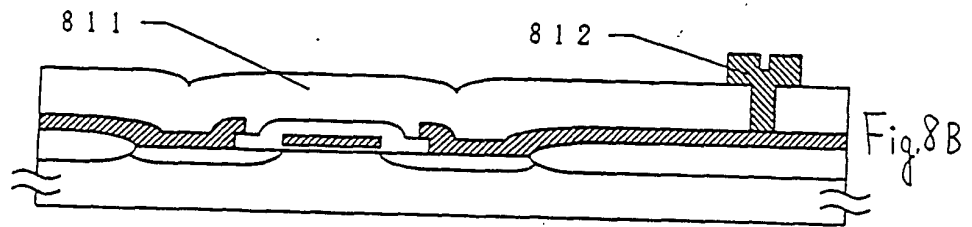
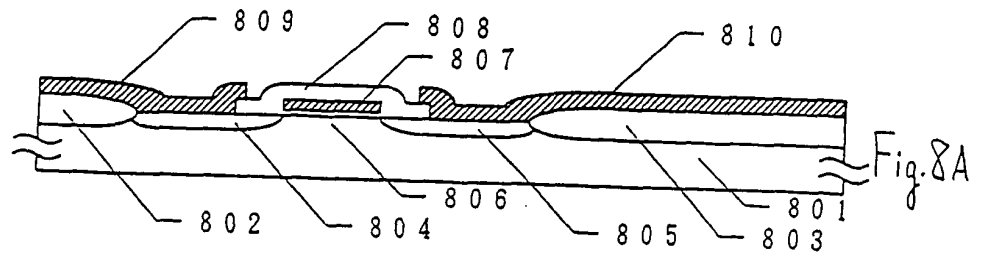
SEMICONDUCTOR THIN FILM AND ITS MANUFACTURING
METHOD AND SEMICONDUCTOR DEVICE AND ITS
MANUFACTURING METHOD

P ION IMPLANTATION

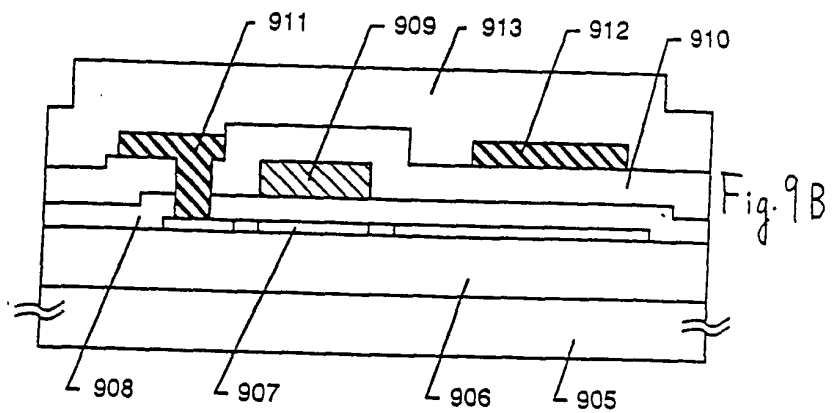
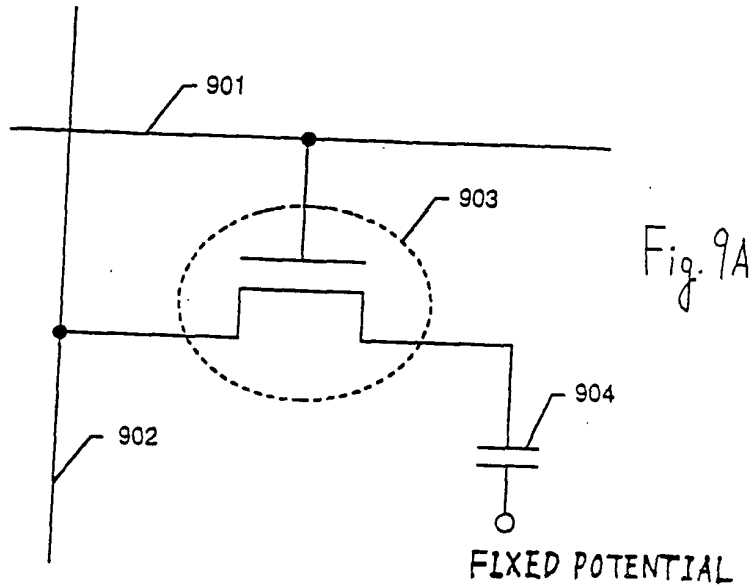




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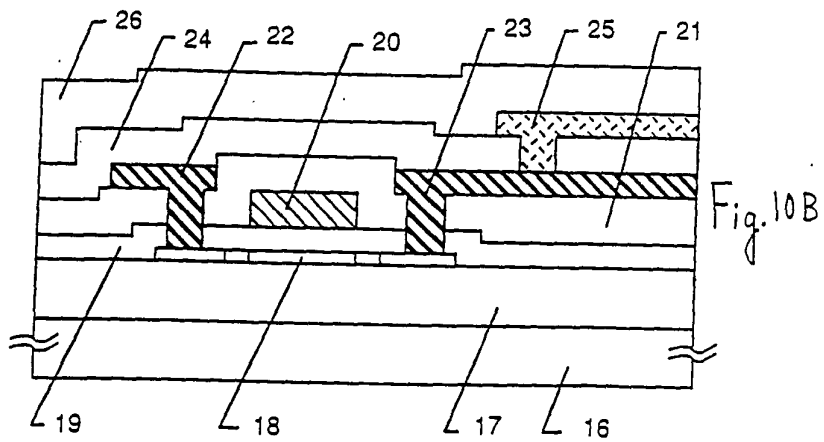
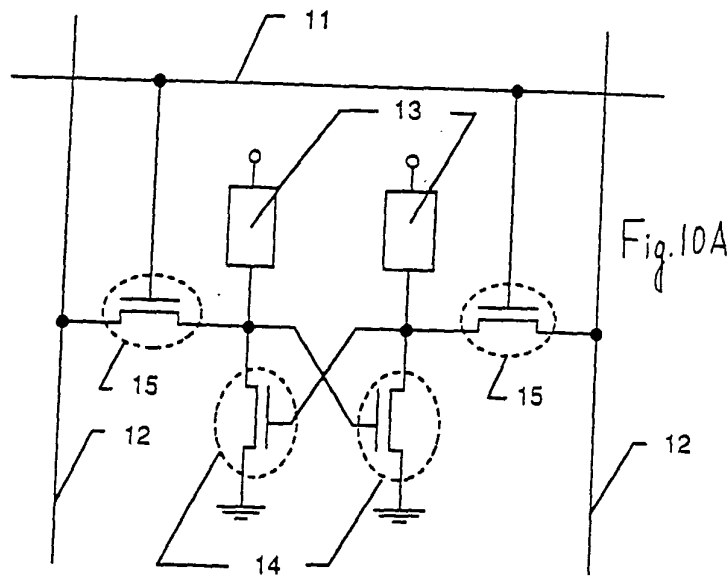
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METHOD AND SEMICONDUCTOR DEVICE AND ITS
MANUFACTURING METHOD

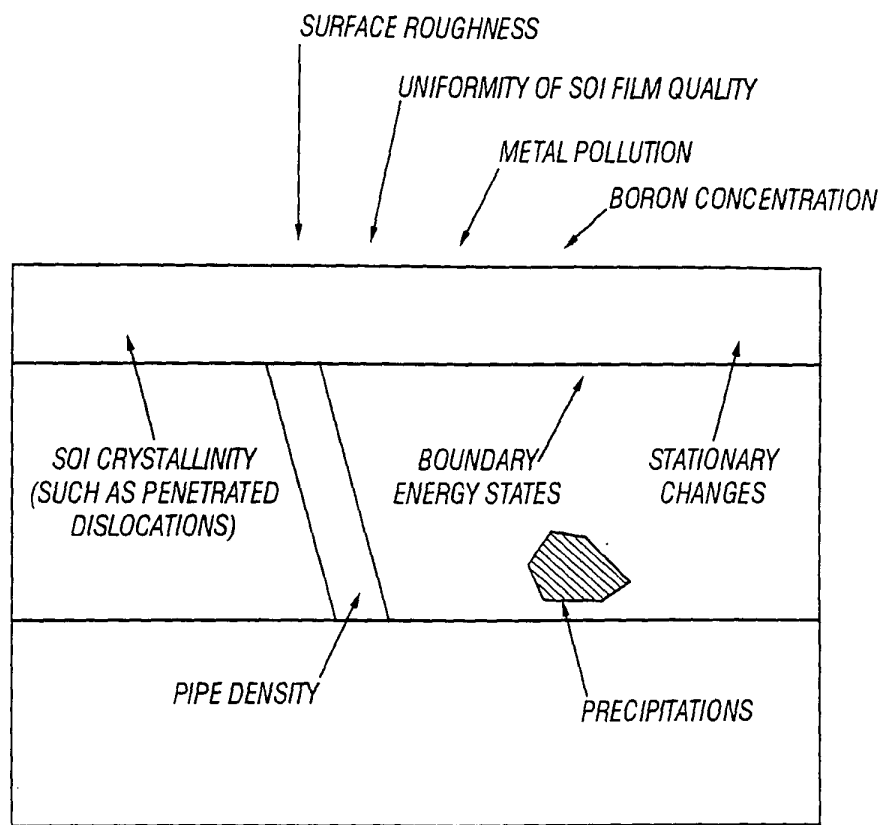
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**FIG. 11**

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SEMICONDUCTOR THIN FILM AND ITS MANUFACTURING
METHOD AND SEMICONDUCTOR DEVICE AND ITS
MANUFACTURING METHOD

Fig. 12

ELE- MENT	CONCENTRATION (PPM)	ELE- MENT	CONCENTRATION (PPM)
Fe	0.045	Ca	0.16
Ni	0.016	Mn	<0.001
Na	>0.005	Al	0.004
K	>0.004	U *2	<0.000031
Ti *1	<0.05	Th *2	<0.00016
Mg	>0.005	F *3	310
Cu	0.009	Cl *2	<0.73
Cr	0.003	OH *4	ND

MEASUREMENT METHOD: POLARIZED ZEEMAN FLAMELESS ATOMIC
ABSORPTION

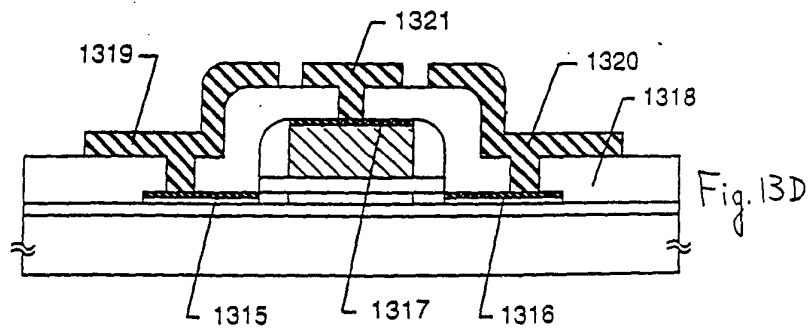
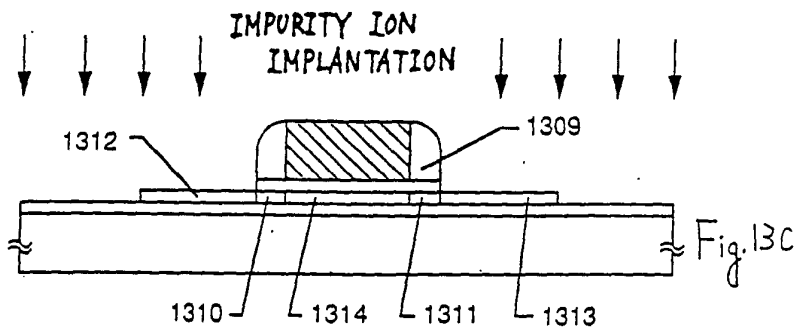
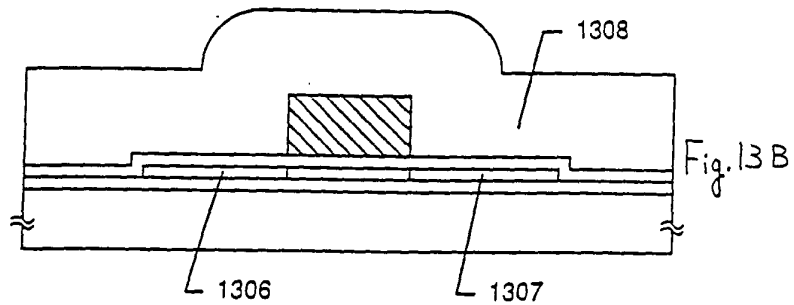
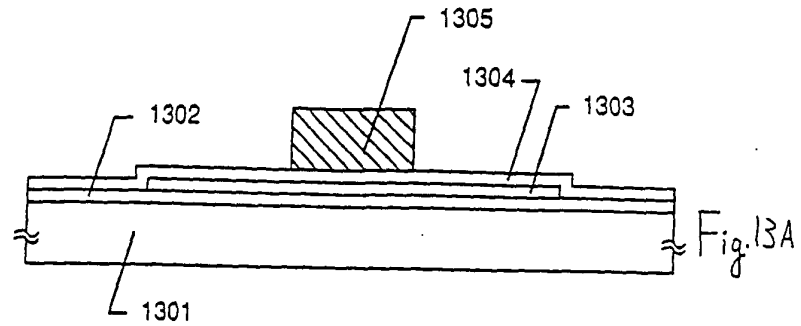
NOTES) *1 ... ICP EMISSION ANALYSIS

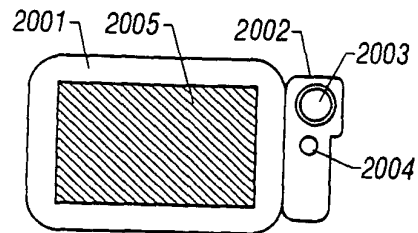
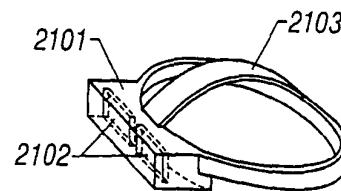
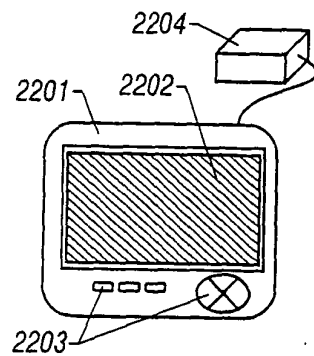
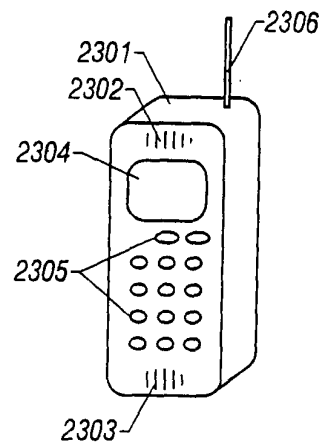
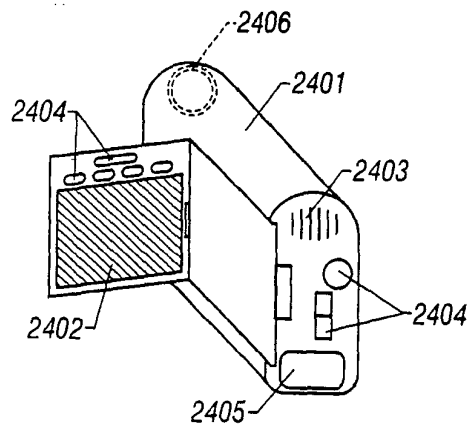
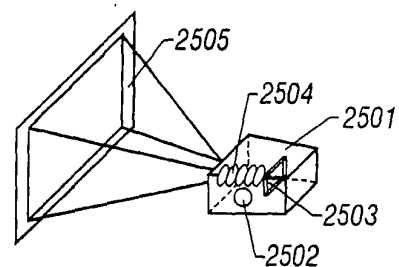
*2 ... RADIOACTIVATION ANALYSIS

*3 .. EPMA

*4 ... INFRARED ABSORPTION

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SEMICONDUCTOR THIN FILM AND ITS MANUFACTURING
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**FIG. 14A****FIG. 14B****FIG. 14C****FIG. 14D****FIG. 14E****FIG. 14F**